

U.S. Department of Commerce, Patent and Trademark Office					Atty Docket No.		Serial No.	
					M-8772 US		09/912,589	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)					Applicant(s)			
					David P. Bour, Nathan F. Gardner, Werner K. Goetz, Stephen A. Stockman, Tetsuya Takeuchi, Ghulam Hasnain, Christopher P. Kocot, Mark R. Hueschen			
					Filing Date		Group	
					July 24, 2001		Unknown	

U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
WSL	AA	6,133,589	10/17/00	Krames et al.	257	103	
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Foreign Patent Documents							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	AL	WO 01/41224 A2	6/7/01	PCT				
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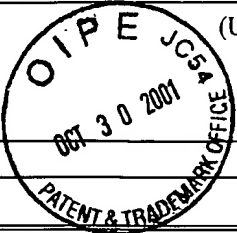
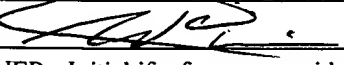
  

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
WSL	AQ	Andreas Hangleiter et al., "The Role Of Piezoelectric Fields In GaN-Based Quantum Wells", MRS Internet J. Nitride Semiconductor Research, 3, 15 (1998), 1998-1999 The Materials Research Society, pp. 1-8.
↓	AR	Fabio Bernardini et al., "Spontaneous Polarization And Piezoelectric Constants Of III-V Nitrides", Vol. 56, No. 16, 15 October 1997, The American Physical Society, 4 pages.
↓	AS	Tetsuya Takeuchi et al., "Determination Of Piezoelectric Fields In Strained GaInN Quantum Wells Using The Quantum-Confined Stark Effect", Applied Physics Letters, Vol. 73, No. 12, 21 September 1998, American Institute of Physics, pp. 1691-1693.

Examiner	<i>[Signature]</i>	Date Considered	9/26/02
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WSL	AQ	S. F. Chichibu et al., "Optical Properties Of InGaN Quantum Wells", Materials Science and Engineering B59 (199) pp. 298-306.						
↓	AR	S. F. Chichibu et al., "Effective Band Gap Inhomogeneity And Piezoelectric Field In InGaN/GaN Multiquantum Well Structures", Applied Physics Letters, Vol. 73, No. 14, 5 October 1998, American Institute of Physics, pp. 2006-2008.						
↓	AS	Takashi Mukai, "Current And Temperature Dependences Of Electroluminescence Of InGaN-Based UV/Blue/Green Light-Emitting Diodes", Japanese Journal of Applied Physics, Vol. 37 (1998) Pt. 2, No. 11B, pp. L1358-L1361.						
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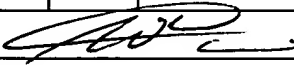
  

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482	AQ	Fabio Della Sala et al., "Free-Carrier Screening Of Polarization Fields In Wurtzite GaN/InGaN Laser Structures", Applied Physics Letters, Vol. 74, No. 14, 5 April 1999, American Institute of Physics, pp. 2002-2004.
↓	AR	L. H. Peng et al., "Piezoelectric Effects In The Optical Properties Of Strained InGaN Quantum Wells", Applied Physics Letters, Vol. 74, No. 6, 8 February 1999, American Institute of Physics, pp. 795-797.
↓	AS	W. W. Chow et al., "Quantum-Well Width Dependence Of Threshold Current Density In InGaN Lasers", Vol. 75, No. 2, 12 July 1999, American Institute of Physics, pp. 244-246.

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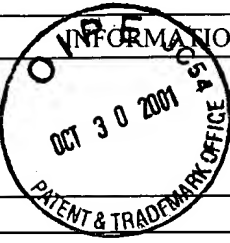
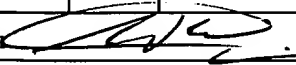
  

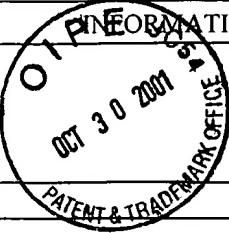
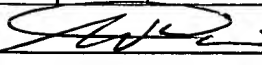
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
WSL	AQ	Shuji Nakamura et al., "Introduction to Nitride Semiconductor Blue Lasers and Light Emitting Diodes", ISBN 0-7484-0836-3, 8 book pages.
↓	AR	Tetsuya Takeuchi et al., "Theoretical Study of Orientation Dependence of Piezoelectric Effects in Wurtzite Strained GaInN/GaN Heterostructures and Quantum Wells", Publication Board, Japanese Journal of Applied Physics, Vol. 39, Part 1, No. 2A, February 2000, pp. 413-416.
↓	AS	Tetsuya Takeuchi et al., "Quantum-Confined Stark Effect Due to Piezoelectric Fields in GaInN Strained Quantum Wells", Japanese Journal of Applied Physics, Vol. 36, Part 2, No. 4A, 1 April 1997, pp.L382-385.

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W82	AQ	K. Horino et al., "Initial Growth Stage of AlGaN Grown Directly on (0001) 6H-SiC By MOVPE", Mat. Res. Soc. Symp. Proc. Vol. 449, 1997 Materials Research Society, pp. 73-78.							
↓	AR	Dongjin Byun et al., "Optimization of the GaN-Buffer Growth on 6H-SiC(0001), Thin Solid Films 289 (1996) pp. 256-260.							
↓	AS	Noriyuki Kiwano et al., "Cross-Sectional TEM Study Of Microstructures In MOVPE GaN Films Grown On $\alpha$ -Al <sub>2</sub> O <sub>3</sub> With A Buffer Layer Of AlN, Journal of Crystal Growth 115 (1991), pp. 381-387.							
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WSL	AQ	Shuji Nakamura, "GaN Growth Using GaN Buffer Layer", Japanese Journal of Applied Physics, Vol. 30, No. 10A, October, 1991, pp. L1705-L1707.						
WSL	AR	H. Amano et al., "Metalorganic Vapor Phase Epitaxial Growth Of A High Quality GaN Film Using An AlN Buffer Layer", Applied Physics Letter, Vol. 48, No. 5, 3 February 1986, pp. 353-355.						
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